

# Atomic Resolution Monitoring of Cation Exchange in CdSe-PbSe Heteronanocrystals during Epitaxial Solid–Solid–Vapor Growth

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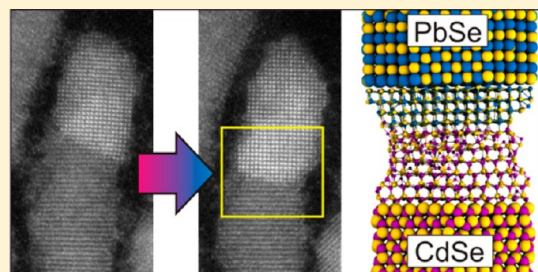
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## Supporting Information

**ABSTRACT:** Here, we show a novel solid–solid–vapor (SSV) growth mechanism whereby epitaxial growth of heterogeneous semiconductor nanowires takes place by evaporation-induced cation exchange. During heating of PbSe–CdSe nanodumbbells inside a transmission electron microscope (TEM), we observed that PbSe nanocrystals grew epitaxially at the expense of CdSe nanodomains driven by evaporation of Cd. Analysis of atomic-resolution TEM observations and detailed atomistic simulations reveals that the growth process is mediated by vacancies.



**KEYWORDS:** Colloidal Nanocrystals, Cation Exchange, Molecular Dynamics, Density Functional Theory, In Situ Transmission Electron Microscopy

Both the synthesis and design of heteronanocrystals (HNCs) have undergone a rapid development, whereby PbSe and CdSe NCs are key materials acting as functional building blocks within a wide variety of heterogeneous nanostructures.<sup>1–8</sup> PbSe–CdSe HNCs are of particular interest as they can exhibit properties different from individual PbSe and CdSe dots. The presence of two semiconductor quantum dots connected via a well-defined interface opens new possibilities for tailoring the optoelectronic properties.<sup>1,4–7,9</sup> Heat treatment of HNCs can induce new interface designs,<sup>5,10–13</sup> exemplified by the transformation of PbSe/CdSe core/shell systems into PbSe–CdSe bihemispheres.<sup>5</sup> Here, we report an in situ heating-induced epitaxial PbSe NC domain growth at the solid–solid PbSe–CdSe nanointerface through cation exchange. We show that Pb replaces Cd at the PbSe/CdSe interface, resulting in growth of the PbSe phase at the expense of the CdSe phase. The incorporated Pb is originating from Pb-oleate present as excess stabilizer at the surface of the mature PbSe/CdSe HNCs.

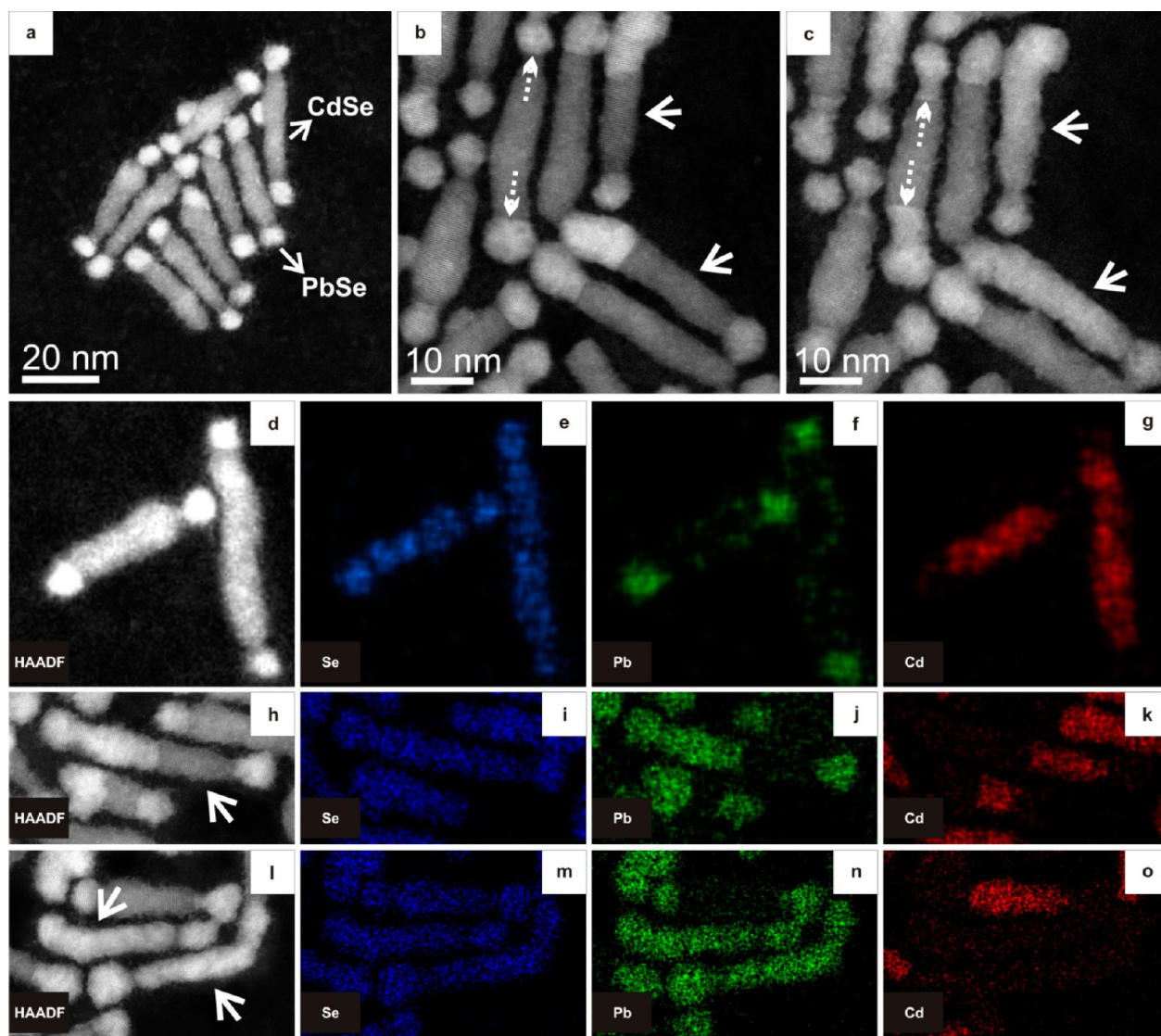
Vapor–liquid–solid (VLS)<sup>14–16</sup> and vapor–solid–solid (VSS)<sup>17,18</sup> growth mechanisms are commonly applied nowadays in nanochemistry to epitaxially grow semiconductor nanowires from the elements dissolved in a liquid (VLS) or solid (VSS) domain. In analogy with these growth mechanisms,

the currently observed process could be called solid–solid–vapor (SSV) growth as the Cd evaporates, either as neutrally charged Cd atoms or in a molecular complex such as Cd-oleate.

Figure 1a shows a HAADF-STEM image (high angle annular dark field scanning transmission electron microscopy) of CdSe–PbSe dumbbell HNCs, consisting of CdSe nanorods with PbSe tips at both ends. In this imaging mode, the intensity scales with  $Z^2$ , where  $Z$  is the atomic number. As Pb has a higher  $Z$  than Cd, PbSe NCs exhibit brighter contrast than the CdSe nanorods. When the HNCs were heated to 160 °C with a heating rate of 10 degrees/min and annealed at this temperature for 5 min, the bright contrast corresponding to PbSe was observed not only at the tips but also extended gradually inside the nanorod domain (solid arrows in Figure 1b), showing that the PbSe phase grows at the expense of the CdSe phase. When the HNCs were heated to 200 °C with the same heating rate and annealed at this temperature for 5 min, the bright contrast was observed over the entire nanorod in some nanorods (solid arrows in Figure 1c). The evolution of this growth was seen to initiate mostly from one PbSe tip

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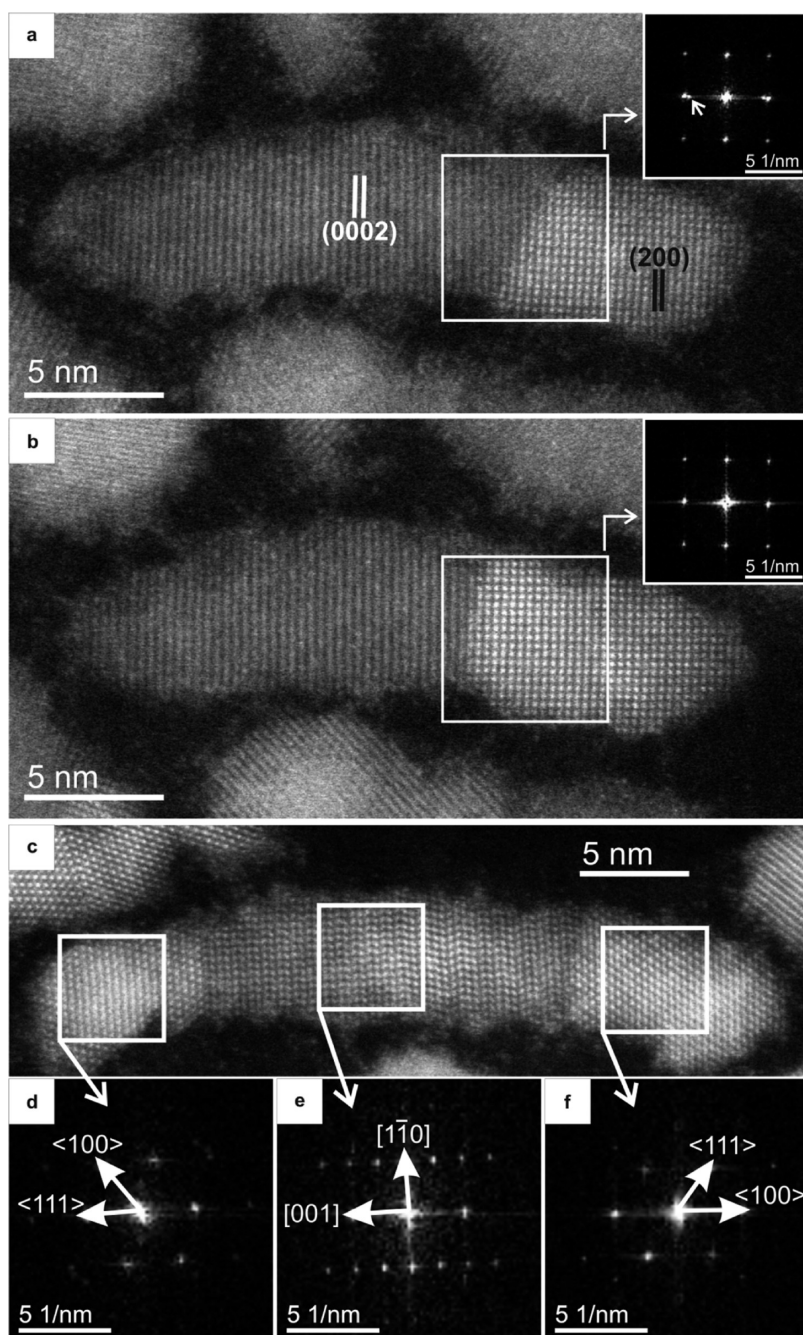
**Figure 1.** HAADF-STEM images and chemical mapping of the nanodumbbells before and after heating. (a) HAADF-STEM image of CdSe-PbSe nanodumbbells. The PbSe tips exhibit brighter contrast than the CdSe nanorods due to Z-contrast. (b,c) Dumbbell HNCs at 160 °C (b) and at 200 °C (c), showing gradual extension of PbSe domains at the expense of CdSe. A heating rate of 10 degrees/min was used in the in situ studies and the HNCs were annealed at the indicated temperatures for 5 min before imaging. Dumbbell HNCs with solid arrows transformed totally to brighter contrast with heating. This phenomenon occurred mostly from one side, though it can proceed from both PbSe domains as well (dumbbell with dashed arrows in panel c). (d–o) HAADF-STEM images and corresponding STEM-EDX elemental maps of dumbbell heteronanostructures annealed for 5 min at temperatures of (d–g) 100 °C, (h–k) 170 °C, and (l–o) 200 °C. In panels d–g, HNCs are in original dumbbell state with PbSe tips and CdSe nanorod. In panels h–k, a partially transformed nanorod is present. In panels l–o, two PbSe–CdSe HNCs became full PbSe domains. The Se remains in place during the transformation. Note that the contrast is maximized in each individual image; hence, intensities of different mappings cannot be directly compared. Quantitative analyses are provided in the Supporting Information.

68 domain (Supporting Information Movies S1 and S2), though it  
69 can also proceed from both PbSe tip domains (dashed arrows  
70 in Figure 1b and c).

71 Chemical mapping by means of energy-dispersive X-ray  
72 spectrometry (EDS) using a Chemi-STEM detector (see  
73 Methods and Supporting Information) was performed to  
74 provide further evidence of the chemical transition. Figure 1d–  
75 g shows the initial state of the HNCs at 100 °C with CdSe  
76 nanorods and PbSe tips. Figure 1f shows that Pb is also present  
77 at the lateral surfaces of the CdSe nanorods, pointing to  
78 adsorbed Pb-oleate molecules. The dumbbell depicted with an  
79 arrow in Figure 1h underwent a transformation, after which half  
80 the nanorod exhibited a bright contrast. With annealing at 170  
81 °C for 5 min, the elemental maps of this dumbbell in Figure

li–k shows that Pb is indeed present in the bright contrast 82  
regions and that Cd is absent. We, therefore, conclude that Cd 83  
started to sublime (as neutral Cd atoms or in a molecular 84  
form) and that at the same time, PbSe was formed by Pb 85  
incorporation. Upon further heating to 200 °C and 5 min 86  
annealing at this temperature, two nanorods (indicated with 87  
arrows in Figure 1l) exhibited a bright contrast over their entire 88  
length. Elemental maps (Figure 1m–o) showed that Cd is no 89  
longer present and the nanorod completely transformed into 90  
PbSe. Disappearance of Cd from a nanostructure was also 91  
reported by De Trizio et al.<sup>12</sup> during a heating of sandwich- 92  
morphology CdSe/Cu<sub>3</sub>P/CdSe HNCs. Note that a complete 93  
transformation occurred very rarely (in about one percent of 94  
the cases). Further heating of partially cation-exchanged 95



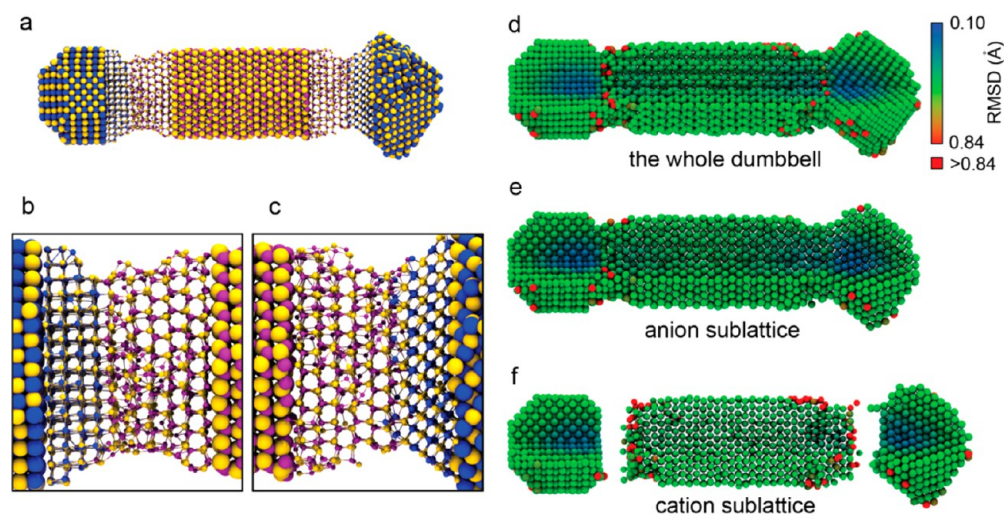


**Figure 2.** Atomic-resolution HAADF-STEM images of CdSe-PbSe HNCs. PbSe has cubic rock salt (RS) crystal structure with a lattice constant<sup>20</sup> of 6.13 Å, whereas CdSe has a hexagonal wurtzite (WZ) crystal structure with lattice parameters<sup>21</sup>  $a = 4.29$  Å and  $c = 7.01$  Å. The CdSe WZ (0002) spacing is 3.5 Å and PbSe RS (200) spacing is 3.1 Å. With heating from 160 °C (a) to 180 °C (b) with a heating rate of 10 degrees/min, WZ CdSe nanorods started to transform to RS PbSe. The insets are Fourier transforms (FTs) taken from the white squares in each image. The spot depicted with an arrow in the inset FT of panel a corresponds to WZ CdSe(0002) spacing. It disappeared in the inset FT of panel b, confirming the WZ to RS transformation. Supporting Information Movie S4 shows the transformation with atomic resolution. (c) HAADF-STEM image of a PbSe-CdSe dumbbell HNC. Stacking faults and a dislocation are present in the CdSe nanorod domain. The interface at the left-hand side is  $\{111\}$ PbSe/ $\{0001\}$ CdSe (panel d), whereas the interface at the right-hand side is  $\{100\}$ PbSe/ $\{0001\}$ CdSe (panel f).

96 nanodumbbells led to dissociation of the domains (Supporting  
97 Information Movie S3). The transformations took place  
98 everywhere on the substrate, not only in areas that were  
99 previously examined with the electron beam. The field of view  
100 was changed frequently in order to avoid beam effects when  
101 monitoring the evolution of the HNCs.

102 As a result of the cation exchange from CdSe to PbSe, the  
103 crystal structure transformed epitaxially from hexagonal

wurtzite (WZ) to cubic rock-salt (RS). Figure 2 and Supporting  
Information Movie S4 show this transformation at atomic  
resolution. When the HNC was heated from 160 °C (Figure  
2a) to 180 °C (Figure 2b) with a heating rate of 10 degrees/  
min, the brighter intensity corresponding to PbSe advanced  
into the CdSe region. The PbSe RS (200) lattice spacings  
started to appear along the nanorod domain instead of the  
CdSe WZ (0002) lattice spacings, as confirmed by the Fourier



**Figure 3.** Force-field MD simulations of the PbSe-CdSe nanodumbbells. (a) Overview image showing the final configuration of a dumbbell obtained after MD simulation at a temperature of 500 K for 5 ns. The ball-stick presentation was used to show the structure of the interfaces. The yellow, purple, and blue spheres are Se, Cd, and Pb atoms, respectively. (b) Magnified image of the  $\{100\}$ PbSe/ $\{0001\}$ CdSe interface at the left-hand side of the dumbbell, and (c) magnified image of the  $\{0001\}$ CdSe/ $\{111\}$ PbSe interface at the right-hand side of the dumbbell. (d,e,f) The map of the root mean square displacement (RMSD) for each atom for the same PbSe-CdSe dumbbell model at 500 K. (d) The whole PbSe-CdSe dumbbell, (e) the anion sublattice, and (f) the cation sublattice. The dumbbell was cut so that both of the surface and inner atoms can be seen. The pure red atoms correspond to those having a RMSD larger than 0.84 Å.

112 transformation (FT) patterns shown in the insets. It is clear  
 113 that the cation exchange takes place at the PbSe/CdSe interface  
 114 and propagates epitaxially (layer by layer) along the WZ  $\langle 0001 \rangle$   
 115 direction. Two types of interfaces were observed:  $\{100\}$ PbSe/  
 116  $\{0001\}$ CdSe and  $\{111\}$ PbSe/ $\{0001\}$ CdSe, similar to the  
 117 interfaces previously reported in the literature for PbSe/CdSe  
 118 and PbS/CdS HNCs.<sup>7,19</sup> Sometimes both types of interfaces  
 119 were observed within one single dumbbell NC. Figure 2c shows  
 120 a HNC with the interfaces of  $\{111\}$ PbSe/ $\{0001\}$ CdSe on the  
 121 left (Figure 2d) and  $\{100\}$ PbSe/ $\{0001\}$ CdSe on the right  
 122 (Figure 2f). It is clear from Figure 2 that epitaxial PbSe growth  
 123 inside CdSe domain via cation exchange can advance from both  
 124 PbSe/CdSe interfaces.

125 Considering the source of Pb that is required for the epitaxial  
 126 PbSe growth in CdSe via cation exchange, we note that PbSe  
 127 NCs with excess Pb surface atoms (off-stoichiometric) have  
 128 been reported in the literature.<sup>22–24</sup> Pb atoms (possibly Pb-  
 129 oleate molecules) are also present along the CdSe nanorods  
 130 (Figure 1f). From the quantification of the elemental maps (see  
 131 Methods and Supporting Information Table S1), it was found  
 132 that the PbSe tips contained an excess of Pb, having a cation/  
 133 anion ratio of  $1.3 \pm 0.2$ . After the transformation, the cation/  
 134 anion ratio at these PbSe tips reduced to  $1.02 \pm 0.14$ . These  
 135 findings indicate Pb diffusion from PbSe tips toward the PbSe/  
 136 CdSe interface. Supporting Information Movie S4 verifies this,  
 137 whereby the bright Pb contrast propagates into the initially  
 138 CdSe nanorod, indicating the epitaxial growth of PbSe, whereas  
 139 the (PbSe) tip domain starts to lose some of its brightness,  
 140 indicating that excess Pb is consumed.

141 In the nanorod domains attached to the PbSe tips where  
 142 cation exchange took place, the cation/anion ratio in the rod  
 143 was reduced to  $0.93 \pm 0.11$  due to Cd sublimation. That most  
 144 nanodumbbells were not completely transformed must, hence,  
 145 be due to the depletion of the source of Pb. The excess Pb  
 146 atoms at the surfaces of the heteronanointerface diffuse toward  
 147 the interface to form new layers of PbSe, but this process stops  
 148 when all excess Pb has been depleted. As mentioned above, a  
 149 complete transformation of the nanorods occurred only rarely.

From an estimate of the number of Pb-oleate molecules that  
 could cover the surface of the nanodumbbells (assuming a high  
 surface density of 5 Pb-oleate molecules per square nano-  
 meter), it was found that for the typical dimensions of the  
 nanodumbbells in this study, the number of surface Pb atoms is  
 not sufficient to replace all the Cd atoms in the CdSe domain  
 (the number of Cd sites is at least two times larger). Therefore,  
 when a complete transformation does occur, likely also Pb  
 atoms from neighboring HNCs will have contributed to the  
 growth of the PbSe domain. This is in agreement with the  
 observation that when the nanodumbbells were lying isolated  
 on the SiN support membrane, the growth process did take  
 place but always resulted in only a partial transformation of the  
 HNCs as shown in Supporting Information Figure S21.

In order to better understand the nanoscopic growth  
 mechanism at the PbSe/CdSe interface, force-field-based MD  
 simulations were performed on HNC models, taking into  
 account various possibilities for the PbSe/CdSe interfacial  
 arrangements (details in Methods and Supporting Informa-  
 tion). Surfactant molecules are not included in the simulation  
 models, and therefore, the MD simulations serve only to study  
 the structure of and atomic mobility at the PbSe/CdSe  
 interfaces. The isolated nanodumbbell models were equi-  
 librated at 300 and 500 K for 5 ns sequentially. Figure 3a shows  
 the final configuration of a nanodumbbell model after 5 ns at  
 500 K. This model has both types of the interfaces  
 ( $\{100\}$ PbSe/ $\{0001\}$ CdSe and  $\{111\}$ PbSe/ $\{0001\}$ CdSe) in  
 one HNC.

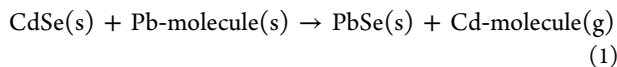
The nanodumbbell model shown in Figure 3 is structurally  
 and morphologically stable at temperatures up to 500 K. The  
 middle part of the CdSe rod and the whole PbSe tips retain  
 their initial WZ and RS structures, respectively. Structural  
 disorder was mainly found in the CdSe domains near the  
 interfaces. Compared to the  $\{100\}$ PbSe/ $\{0001\}$ CdSe interface,  
 the CdSe domain near the  $\{111\}$ PbSe/ $\{0001\}$ CdSe interface is  
 more structurally ordered. In the latter case, most of the Cd  
 and Se atoms remain at the WZ lattice sites, which is likely due to  
 the fact that the cation-terminated  $\{0001\}$ CdSe surface and the



188 anion-terminated {111}PbSe surface form a continuous polar/  
189 polar interface, whereas the lattice mismatch is small. In  
190 contrast, the {100}PbSe/{0001}CdSe interface is a nonpolar/  
191 polar interface, which leads to stronger distortions in the atomic  
192 lattice due to Coulombic interactions. The simulations  
193 therefore suggest that the transformation at the {100}PbSe/  
194 {0001}CdSe interface will be more efficient than at the  
195 {111}PbSe/{0001}CdSe interface, although this could not be  
196 confirmed by the experiments as the orientation of the two  
197 crystals could be determined only in a limited number of cases.  
198 Not only is the atomic structure more disordered in the CdSe  
199 domains near the {100}PbSe/{0001}CdSe interfaces (see  
200 Supporting Information Figure S22 for a planar view of the  
201 atomic bilayers parallel to the interface), the simulations also  
202 show an unusually high mobility of the Cd atoms in the few  
203 first atomic layers from the PbSe/CdSe interface, as evidenced  
204 by the map of the root mean square displacement (RMSD) for  
205 each atom (Figure 3d–f). Those atoms with the highest  
206 mobility (red atoms) are mostly Cd atoms near the interfaces  
207 or on the surface, indicating that the cation exchange occurs  
208 only very close to the interface.

209 The experimental observations and the MD simulations  
210 suggest that the transformation is mediated by vacancies in the  
211 Cd and Pb sublattices; evaporation of Cd results in Cd  
212 vacancies at the CdSe surface. After migration of these Cd  
213 vacancies to the PbSe/CdSe interface, Pb atoms can jump into  
214 the vacant sites, thereby leaving behind vacancies on the Pb  
215 sublattice, which will eventually recombine with excess Pb  
216 absorbed at the surface of the PbSe domain. Density functional  
217 theory (DFT) calculations of defect energies (see Section F in  
218 Supporting Information) confirm that upon evaporation of Cd,  
219 both in CdSe and PbSe the defect energetics are ruled by  
220 vacancies. The DFT calculations also show (Supporting  
221 Information Table S10) that the Se-Frenkel defect energy (Se  
222 vacancy + Se interstitial) is considerably higher (6.00 for CdSe  
223 and 3.80 eV for PbSe) than the Cd-Frenkel and Pb-Frenkel  
224 defect energies (3.16 and 3.30 eV, respectively). It is, thus,  
225 energetically much more expensive to create defects on the Se  
226 sublattice. Because the Se sublattice is not much affected by the  
227 cation exchange that takes place on the (Pb,Cd) sublattice, the  
228 crystallographic orientation relation between the CdSe and  
229 PbSe nanodomains is retained during the transformation. This  
230 is the reason that the growth process is epitaxial in nature.

231 The most important driving force for the growth process is  
232 the evaporation of Cd. It is well known that a chemical reaction  
233 can be efficiently driven into one direction by bringing one  
234 reaction product in the gas phase. Assuming that the excess Pb  
235 originates from Pb-oleate coverage of the HNC and that the Cd  
236 evaporates in a molecular form, the chemical reaction can be  
237 summarized as follows:



239 In the CdSe lattice, the Cd and Se atoms can be modeled as  
240 ions. Bader charge analysis (details in Section E of the  
241 Supporting Information) performed on the electronic charge  
242 density obtained from DFT calculations shows that the effective  
243 charge of the Cd cation in CdSe bulk is approximately +0.8e.  
244 However, the Cd will evaporate only as a neutral species.  
245 Because the transition from a charged  $\text{Cd}^{+0.8}$  ion to a neutral  
246  $\text{Cd}^0$  atom would require the nanocrystal to donate electrons,  
247 we consider it more likely that Cd at the surface of the  
248 nanocrystal binds to the surfactants (e.g., oleate), followed by

evaporation. We mention here that heating in vacuum is an  
efficient method to detach surfactants from nanocrystals.<sup>20,25</sup>

From the available experimental and simulation data, a  
mechanism can now be deduced to describe the cation  
exchange. All processes take place close to the interfaces in a  
fast and volatile manner as demonstrated by Supporting  
Information Movie S4. The growth mechanism is shown  
schematically in Figure S1 of the Supporting Information and  
can be summarized as follows. (i) Cd sublimates from the  
surface of the CdSe nanodomains, whereby Cd vacancies are  
formed. (ii) The Cd vacancies occupy positions at the CdSe  
side of the PbSe/CdSe interface (Figure 3 and Supporting  
Information Figure S22). (iii) Cation replacement takes place  
as Pb atoms jump into vacant Cd sites in a layer by layer  
fashion, resulting in epitaxial growth of RS PbSe at the expense  
of WZ CdSe. (iv) The jumping Pb atoms leave behind  
vacancies, which migrate to the PbSe surface. (v) The Pb  
vacancies at the surface recombine with Pb ions from adsorbed  
Pb-oleate molecules. The oleate molecule remains adsorbed at  
the PbSe surface and possibly migrates to the CdSe domain  
where it combines with Cd and evaporates as Cd-oleate. (vi)  
The process is halted when the excess Pb (in the form of Pb-  
oleate molecules) in the system is depleted.

The atomistic mechanism described here most likely also  
takes place when HNCs undergo cation exchange in colloidal  
solutions, whereby instead of evaporating, the metal-molecule  
complex is dissolved in the solution. In the current solid–  
solid–vapor (SSV) growth mechanism, one solid phase grows  
epitaxially at the expense of another solid phase, efficiently  
driven by evaporation of one element (here, Cd) with  
simultaneous supply of another element (here, Pb coordinated  
with a molecule). Our results show that SSV growth can  
provide an alternative path for growing heterogeneous  
semiconductor nanowires, especially when the lattices have a  
partly ionic character, and therefore holds promise for  
generating new families of heterogeneous nanostructures.

## METHODS

The synthesis of PbSe/CdSe dumbbell nanostructures is  
detailed in the Supporting Information. TEM specimens were  
prepared by dropcasting 8  $\mu\text{L}$  of the NC colloidal solution onto  
a MEMS microhot plate with electron-transparent SiN  
membranes, which was mounted onto a DENSolutions low  
drift TEM heating holder.<sup>25</sup> After dropcasting, the sample was  
plasma cleaned for 10 s in order to remove deposits from the  
solution that prevent high-resolution imaging in the TEM. The  
in situ experiments were performed in a 80–300 FEI Titan  
microscope equipped with a Chemi-STEM EDX detection  
system. During HAADF-STEM imaging, the microscope was  
operated at 300 kV. The camera length used in the experiments  
equals 91 mm in order to avoid diffraction effects and to  
guarantee Z-contrast imaging. In HAADF-STEM imaging, the  
intensity approximately scales with  $Z^2$ . As Pb has a higher Z  
number than Cd, the PbSe domains appear with higher  
intensity in HAADF-STEM images in comparison to the CdSe  
domains.

The Chemi-STEM EDS experiments were performed using  
the same holder and in the same 80–300 FEI Titan microscope  
but were operated at a lower acceleration voltage of 200 kV to  
reduce beam damage during mapping. A beam current of  
approximately 250 pA was used during acquisition. A  
representative spectrum is shown in Supporting Information  
Supplementary Figure S20. In the quantification of the 310

311 elemental maps, 18 PbSe NC maps were used to determine the  
312 cation/anion ratio at the PbSe tips at the initial state. For the  
313 PbSe tips from where cation exchange proceeded, the elemental  
314 composition of 10 different PbSe tips was quantified. For the  
315 nanorod domains attached to the PbSe tips where cation  
316 exchange took place, the elemental composition of 10 different  
317 nanorod (transformed)-domains were quantified. Additional  
318 TEM images, chemical maps, and quantitative analysis are  
319 provided in Figures S2–S19 and Tables S1–S6 of the  
320 Supporting Information.

321 For the force-field MD simulations, a new interaction  
322 potential model for the Pb–Cd–Se system was developed.  
323 The potential was found to accurately describe physical  
324 parameters such as lattice parameters, elastic constants, and  
325 the relative stability of phases. Details of the potential model  
326 (Supporting Information Table S7) and a description of the  
327 nanodumbbell models are given in Section E of the Supporting  
328 Information. For simulations of the nanodumbbells, Coulomb  
329 and short-range interactions were calculated by taking into  
330 account all atom pairs. The equations of motion were  
331 integrated using the velocity Verlet algorithm with a time  
332 step of 1 fs. Periodic boundary conditions were not used and  
333 the nanodumbbell models were isolated in vacuum. Simulations  
334 of 5 ns were carried out in the NVT ensemble and 1 ns was  
335 used for equilibration.

336 All density functional theory (DFT) calculations on defect  
337 energies and energies of mixed PbSe–CdSe phases were carried  
338 out using the first-principles' Vienna Ab Initio Simulation  
339 Program (VASP)<sup>26</sup> using the projector augmented wave  
340 (PAW) method.<sup>27</sup> The generalized gradient approximation  
341 (GGA) formulated by Perdew, Burke, and Ernzerhof (PBE)<sup>28</sup>  
342 was employed for the exchange and correlation energy terms.  
343 The cutoff energy of the wave functions was 350.0 eV. The  
344 cutoff energy of the augmentation functions was about 500.0  
345 eV. The electronic wave functions were sampled on a  $4 \times 4 \times 2$   
346 grid using the Monkhorst and Pack method with 8 to 20  $k$ -  
347 points depending on different symmetries of supercells (108  
348 atoms). Structural optimizations were performed for both  
349 lattice parameters and coordinates of atoms. Different  $k$ -meshes  
350 and cutoff energies for waves were tested to have a good  
351 convergence (<2 meV/atom). Details are given in the  
352 Supporting Information.

## 353 ■ ASSOCIATED CONTENT

### 354 ● Supporting Information

355 Includes four movies (Movies S1, S2, S3, and S4), a description  
356 of the synthesis of the PbSe/CdSe HNCs, additional HAADF-  
357 STEM images, STEM-EDX chemical maps and quantification,  
358 force field MD simulations, and DFT calculations of the defect  
359 energies and mixed PbSe–CdSe phases. This material is  
360 available free of charge via the Internet at <http://pubs.acs.org>.

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### 366 Notes

367 The authors declare no competing financial interest.

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## 388 ■ REFERENCES

- 389 (1) Son, D. H.; Hughes, S. M.; Yin, Y.; Alivisatos, A. P. *Science* **2004**,  
390 306, 1009–1012.
- 391 (2) Robinson, R. D.; Sadtler, B.; Demchenko, D. O.; Erdonmez, C.  
392 K.; Wang, L.-W.; Alivisatos, A. P. *Science* **2007**, 317, 355–358.
- 393 (3) Bals, S.; Casavola, M.; van Huis, M. A.; Van Aert, S.; Batenburg,  
394 K. J.; Van Tendeloo, G.; Vanmaekelbergh, D. *Nano Lett.* **2011**, 11,  
395 3420–3424.
- 396 (4) Casavola, M.; van Huis, M. A.; Bals, S.; Lambert, K.; Hens, Z.;  
397 Vanmaekelbergh, D. *Chem. Mater.* **2012**, 24, 294–302.
- 398 (5) Grodzińska, D.; Pietra, F.; van Huis, M. A.; Vanmaekelbergh, D.;  
399 de Mello Donegá, C. *J. Mater. Chem.* **2011**, 21, 11556–11565.
- 400 (6) Zhang, Y.; Dai, Q.; Li, X.; Cui, Q.; Gu, Z.; Zou, B.; Wang, Y.; Yu,  
401 W. W. *Nanoscale Res. Lett.* **2010**, 5, 1279–1283.
- 402 (7) Kudera, S.; Carbone, L.; Casula, M. F.; Cingolani, R.; Falqui, A.;  
403 Snoeck, E.; Parak, W. J.; Manna, L. *Nano Lett.* **2005**, 5, 445–449.
- 404 (8) Overgaag, K.; Evers, W.; de Nijs, B.; Koole, R.; Meeldijk, J.;  
405 Vanmaekelbergh, D. *J. Am. Chem. Soc.* **2008**, 130, 7833–7835.
- 406 (9) Grodzińska, D.; Evers, W. H.; Dorland, R.; van Rijssel, J.; van  
407 Huis, M. A.; Meijerink, A.; de Mello Donegá, C.; Vanmaekelbergh, D.  
408 *Small* **2011**, 7, 3493–3501.
- 409 (10) van Huis, M. A.; Figuerola, A.; Fang, C.; Béché, A.; Zandbergen,  
410 H. W.; Manna, L. *Nano Lett.* **2011**, 11, 4555–4561.
- 411 (11) Figuerola, A.; van Huis, M.; Zanella, M.; Genovese, A.; Marras,  
412 S.; Falqui, A.; Zandbergen, H. W.; Cingolani, R.; Manna, L. *Nano Lett.*  
413 **2010**, 10, 3028–3036.
- 414 (12) De Trizio, L.; De Donato, F.; Casu, A.; Genovese, A.; Falqui, A.;  
415 Povia, M.; Manna, L. *ACS Nano* **2013**, 7, 3997–4005.
- 416 (13) Yalcin, A. O.; de Nijs, B.; Fan, Z.; Tichelaar, F. D.;  
417 Vanmaekelbergh, D.; van Blaaderen, A.; Vlugt, T. J. H.; van Huis,  
418 M. A.; Zandbergen, H. W. *Nanotechnology* **2014**, 25, 055601.
- 419 (14) Wagner, R. S.; Ellis, W. C. *Appl. Phys. Lett.* **1964**, 4, 89–90.
- 420 (15) Gudiksen, M. S.; Lauhon, L. J.; Wang, J.; Smith, D. C.; Lieber,  
421 C. M. *Nature* **2002**, 415, 617–620.
- 422 (16) Wang, H.; Zepeda-Ruiz, L. A.; Gilmer, G. H.; Upmanyu, M. *Nat.*  
423 *Commun.* **2013**, 4, 1956.
- 424 (17) Persson, A. I.; Larsson, M. W.; Stenström, S.; Ohlsson, B. J.;  
425 Samuelson, L.; Wallenberg, L. R. *Nat. Mater.* **2004**, 3, 677–681.
- 426 (18) Campos, L. C.; Tonezzer, M.; Ferlauto, A. S.; Grillo, V.;  
427 Magalhães-Paniago, R.; Oliveira, S.; Ladeira, L. O.; Lacerda, R. G. *Adv.*  
428 *Mater.* **2008**, 20, 1499–1504.
- 429 (19) Luther, J. M.; Zheng, H.; Sadtler, B.; Alivisatos, A. P. *J. Am.*  
430 *Chem. Soc.* **2009**, 131, 16851–16857.

- 431 (20) van Huis, M. A.; Kunneman, L. T.; Overgaag, K.; Xu, Q.;  
432 Pandraud, G.; Zandbergen, H. W.; Vanmaekelbergh, D. *Nano Lett.*  
433 **2008**, *8*, 3959–3963.
- 434 (21) Xu, Y.-N.; Ching, W. Y. *Phys. Rev. B: Condens. Matter Mater.*  
435 *Phys.* **1993**, *48*, 4335–4351.
- 436 (22) Moreels, I.; Lambert, K.; De Muynck, D.; Vanhaecke, F.;  
437 Poelman, D.; Martins, J. C.; Allan, G.; Hens, Z. *Chem. Mater.* **2007**, *19*,  
438 6101–6106.
- 439 (23) Moreels, I.; Fritzing, B.; Martins, J. C.; Hens, Z. *J. Am. Chem.*  
440 *Soc.* **2008**, *130*, 15081–15086.
- 441 (24) Petkov, V.; Moreels, I.; Hens, Z.; Ren, Y. *Phys. Rev. B: Condens.*  
442 *Matter Mater. Phys.* **2010**, *81*, 241304.
- 443 (25) van Huis, M. A.; Young, N. P.; Pandraud, G.; Creemer, J. F.;  
444 Vanmaekelbergh, D.; Kirkland, A. I.; Zandbergen, H. W. *Adv. Mater.*  
445 **2009**, *21*, 4992–4995.
- 446 (26) Kresse, G.; Hafner, J. *Phys. Rev. B: Condens. Matter Mater. Phys.*  
447 **1993**, *47*, 558–561.
- 448 (27) Kresse, G.; Joubert, D. *Phys. Rev. B: Condens. Matter Mater. Phys.*  
449 **1999**, *59*, 1758–1775.
- 450 (28) Perdew, J. P.; Burke, K.; Ernzerhof, M. *Phys. Rev. Lett.* **1996**, *77*,  
451 3865–3868.